

60V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -60V
- BV_{ECO} > -7V
- I_C = 5A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < -80mV @ 1A
- R_{CE(sat)} = 50mΩ
- Complementary PNP Type: ZXTN19060CG
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

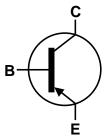
Applications

- Motor Drive
- High Side Driver

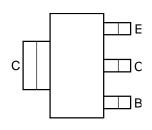




Top View



Device Symbol



Top View Pin-Out

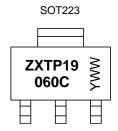
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP19060CGTA	AEC-Q101	ZXTP19060C	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXTP19060C = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Collector Voltage (reverse blocking)	V _{ECX}	-7	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-5	Α
Base Current	I _B	-1	Α
Peak Pulse Current	I _{CM}	-7	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		1.2 9.6	
Power Dissipation	(Note 6)		1.6 12.8	w
Linear Derating Factor	(Note 7)	PD	3 24	mW/°C
	(Note 8)		5.3 42	
	(Note 5)		104	
The word Desistance Investigate Ambient	(Note 6)		78	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	42	°C/W
	(Note 8)		23.5	
Thermal Resistance, Junction to Lead (Note 9)		R _{0JL}	16	1
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

Notes:

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air

conditions whilst operating in steady-state.
6. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.

^{7.} Same as Note 6, except the device is mounted on 50mm x 50mm 2oz copper.

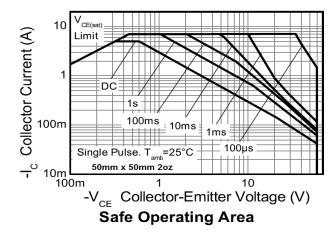
^{8.} Same as Note 8 measured at t<5 seconds.

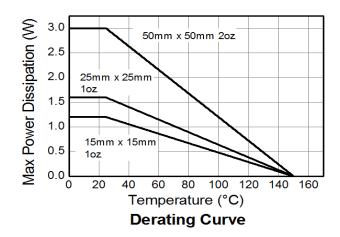
^{9.} Thermal resistance from junction to solder-point (at the end of the collector lead).

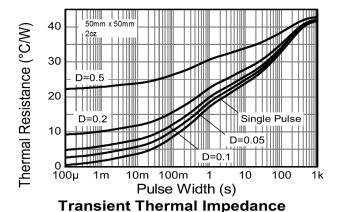
^{10.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.

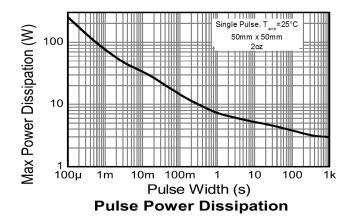


Thermal Characteristics and Derating Information (@T_A = +25°C, unless otherwise specified.)













Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

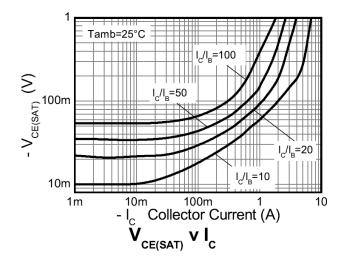
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-60	-110	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-60	-90	_	V	$I_C = -10mA$
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECX}	-7	-8.4	_	V	$I_C = -100\mu A$, $R_{BC} < 1k\Omega$ or 0.25V< $V_{BC} > -0.25V$
Emitter-Collector Breakdown Voltage (reverse blocking)	BV_{ECO}	-7	-8.8	_	V	I _E = -100μA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.4	_	V	I _E = -100μA
Collector Cut-Off Current	1	-	< 1	-50	nA	V _{CB} = -60V
Collector Cut-Oil Current	I _{CBO}	_	_	-0.5	μA	V _{CB} = -60V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	-	< 1	-50	nA	V _{EB} = -5.6V
	VCE(sat)	-	-62	-80	mV	I _C = -1A, I _B = -100mA
		_	-145	-205	mV	I _C = -1A, I _B = -20mA
Collector-Emitter Saturation Voltage (Note 11)		_	-500	-750	mV	$I_C = -2A$, $I_B = -40mA$
Collector-Emilier Saturation voltage (Note 11)		_	-105	-165	mV	$I_C = -2A$, $I_B = -200mA$
		-	-145	-200	mV	$I_C = -3A$, $I_B = -300mA$
		-	-300	-500	mV	$I_C = -5A$, $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	-975	-1050	mV	$I_C = -5A$, $I_B = -500mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	-	-890	-1000	mV	$I_{C} = -5A$, $V_{CE} = -2V$
	h _{FE}	200	330	500	ı	$I_C = -100 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain (Note 11)		160	260	-	=	$I_C = -1A$, $V_{CE} = -2V$
		20	40	-	ı	$I_C = -5A$, $V_{CE} = -2V$
Current Gain-Bandwidth Product (Note 11)	f _T	_	180	_	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 50MHz
Input Capacitance (Note 11)	C_{ibo}	-	280	400	рF	$V_{EB} = -0.5V, f = 1MHz$
Output Capacitance (Note 11)	C_obo	_	29.5	40	pF	$V_{CB} = -10V$, $f = 1MHz$
Delay Time	t _d	-	24.3	-	ns	
Rise Time	t _r	-	13.2	-	ns	$I_C = -500 \text{mA}, V_{CC} = -10 \text{V},$
Storage Time	ts	-	456	-	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Fall Time	t _f	-	68.2	_	ns	

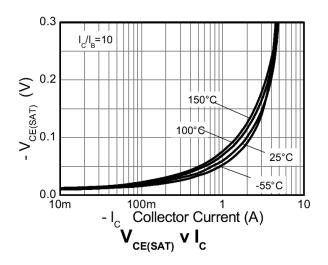
Note:

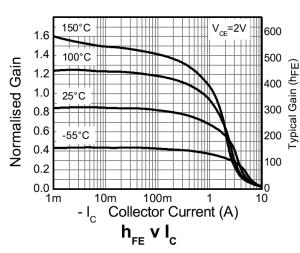
11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

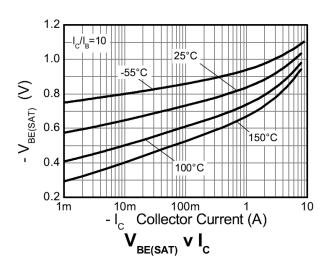


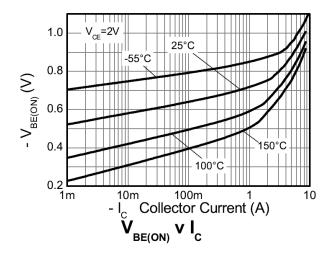
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

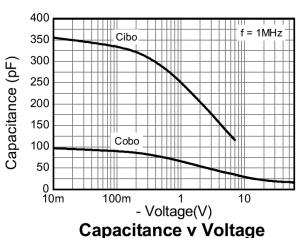








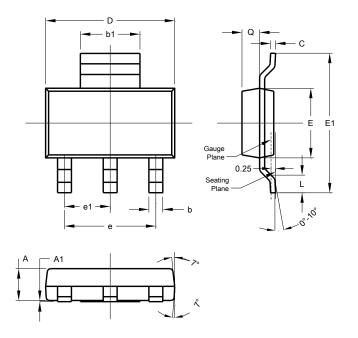






Package Outline Dimensions

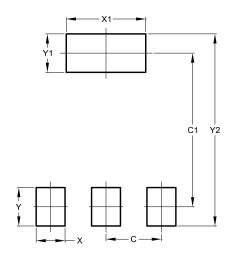
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		





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